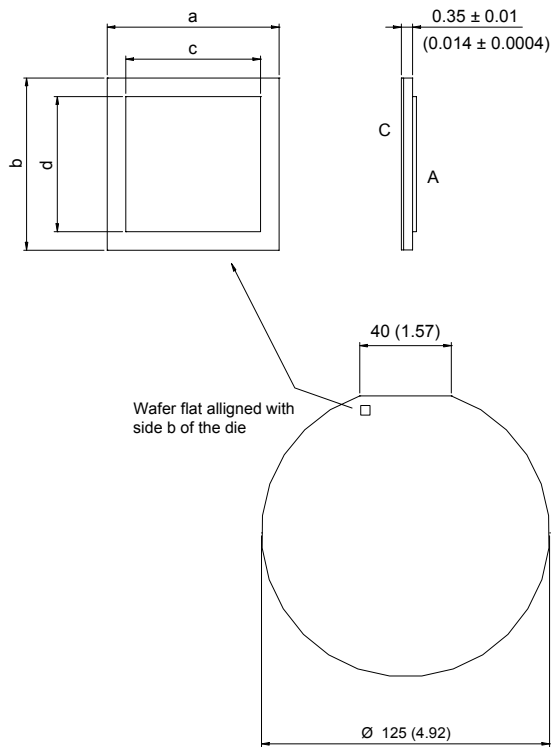


International
IR Rectifier

FD120H06A5B

Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

2. CONTROLLING DIMENSION (INCH):

3. DIMENSIONS AND TOLERANCES:

a = 3.048 ± 0.05

(0.120 ± 0.002)

b = 3.048 ± 0.05

(0.120 ± 0.002)

c = 2.388 ± 0.003

(0.094 ± 0.0001)

d = 2.388 ± 0.003

(0.094 ± 0.0001)

4. LETTER DESIGNATION:

A = Anode (Top Metal)

C = Cathode (Back Metal)

5. SAWING:

Recommended Blade

SEMITEC S1025 QS00 Blade

6. MINIMUM ORDER QUANTITY:

900 die

NOT TO SCALE

Reference IR Packaged Part: 15ETH06 Series

Electrical Characteristics (Wafer Form)

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	2.3 V	$T_J = 25^\circ\text{C}$, $I_F = 15\text{ A}$
V_{RRM} Minimum Reverse Breakdown Voltage	600 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 200\text{ }\mu\text{A}$
I_{RM} Max. Reverse Leakage Current	100 μA	$T_J = 25^\circ\text{C}$, $V_{RRM} = 600\text{ V}$
t_{rr} Typ. Reverse Recovery Time	20 ns	$I_F = 1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.120" x 0.120" (see drawing)
Reject Ink Dot Size	0.25 mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code						
	FD	120	H	06	A	5 B
	①	②	③	④	⑤	⑥ ⑦
1	- Fred Die					
2	- Chip Dimension in Mils: 120 = 120x120 square					
3	- Process H = HyperFast					
4	- Voltage code Vrrm (*100) eg: 06 = 600V					
5	- Chip surface metallization: A = Aluminium (anode), Silver (cathode)					
6	- Wafer diameter in inches					
7	- Packaging: B = Inked Probed Unsawn Wafer (Wafer in box)					